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Kind regards,

Team Nexperia

PMEG4010EH; PMEG4010EJ; PMEG4010ET

1 A very low V_F MEGA Schottky barrier rectifiers

Rev. 04 — 21 March 2007

Product data sheet

1. Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection, encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			Configuration
	NXP	JEITA	JEDEC	
PMEG4010EH	SOD123F	-	-	single
PMEG4010EJ	SOD323F	SC-90	-	single
PMEG4010ET	SOT23	-	TO-236AB	single

1.2 Features

Forward current: I_F ≤ 1 A

Reverse voltage: V_R ≤ 40 V

Very low forward voltage

Small SMD plastic packages

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current	$T_{sp} \le 55 ^{\circ}C$	-	-	1	Α
V_R	reverse voltage		-	-	40	V
V _F	forward voltage	$I_F = 1000 \text{ mA}$	<u>[1]</u> _	540	640	mV

[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



2. Pinning information

Table 3. Pinning

Table 3. I	iii		
Pin	Description	Simplified outline	Symbol
SOD123F; S	OD323F		
1	cathode	[1]	8.4
2	anode	001aab540	1 2 2 sym001
SOT23			
1	anode		
2	n.c.	3	3
3	cathode	1 2	1 2 n.c. 006aaa436

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 4. Ordering information

Type number	ber Package				
	Name	Description	Version		
PMEG4010EH	-	plastic surface-mounted package; 2 leads	SOD123F		
PMEG4010EJ	SC-90	plastic surface-mounted package; 2 leads	SOD323F		
PMEG4010ET	-	plastic surface-mounted package; 3 leads	SOT23		

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PMEG4010EH	AB
PMEG4010EJ	AL
PMEG4010ET	*AW

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage			-	40	V
I _F	forward current	T _{sp} ≤ 55 °C		-	1	Α
I _{FRM}	repetitive peak forward current	$t_p \le 1$ ms; $\delta \le 0.25$				
	PMEG4010EH			-	7	Α
	PMEG4010EJ			-	7	Α
	PMEG4010ET			-	5	Α
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms		-	9	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$				
	PMEG4010EH		[1][3]	-	375	mW
			[2][3]	-	830	mW
	PMEG4010EJ		[1][3]	-	350	mW
			[2][3]	-	830	mW
	PMEG4010ET		<u>[1]</u>	-	280	mW
			[2]	-	420	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C
T _{stg}	storage temperature			-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[3] Reflow soldering is the only recommended soldering method.

6. Thermal characteristics

Table 7. Thermal characteristics

Table 1.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PMEG4010EH		[2][4]	-	330	K/W
			[3][4]	-	150	K/W
	PMEG4010EJ		[2][4]	-	350	K/W
			[3][4]	-	150	K/W
	PMEG4010ET		[2] _	-	440	K/W
			[3] _	-	300	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[5]</u>			
	PMEG4010EH		-	-	60	K/W
	PMEG4010EJ		-	-	55	K/W
	PMEG4010ET		-	-	120	K/W

^[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

7. Characteristics

 Table 8.
 Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage		<u>[1]</u>			
		$I_F = 0.1 \text{ mA}$	-	95	130	mV
		$I_F = 1 \text{ mA}$	-	155	210	mV
		$I_F = 10 \text{ mA}$	-	220	270	mV
		$I_F = 100 \text{ mA}$	-	295	350	mV
		$I_F = 500 \text{ mA}$	-	420	470	mV
		$I_F = 1000 \text{ mA}$	-	540	640	mV
I _R	reverse current	$V_R = 10 V$	-	7	20	μΑ
		$V_R = 40 V$	-	30	100	μΑ
C _d	diode capacitance	$V_R = 1 V;$ f = 1 MHz	-	43	50	pF

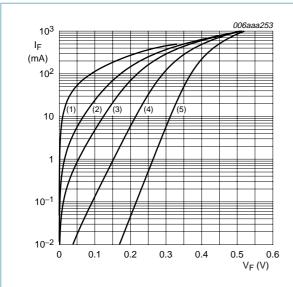
^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

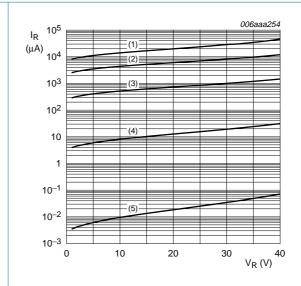
^[4] Reflow soldering is the only recommended soldering method.

^[5] Soldering point of cathode tab.



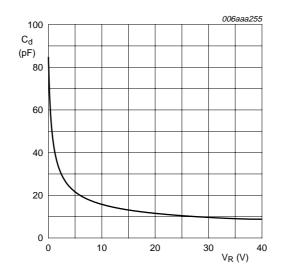
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \,^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 125 \, ^{\circ}C$
- (3) $T_{amb} = 85 \, ^{\circ}C$
- (4) $T_{amb} = 25 \,^{\circ}C$
- (5) $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values

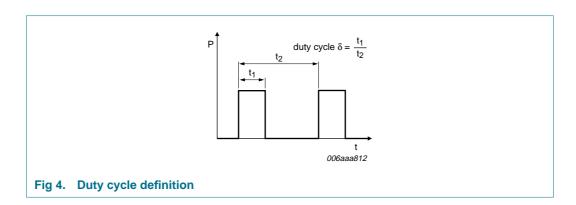


f = 1 MHz; T_{amb} = 25 °C

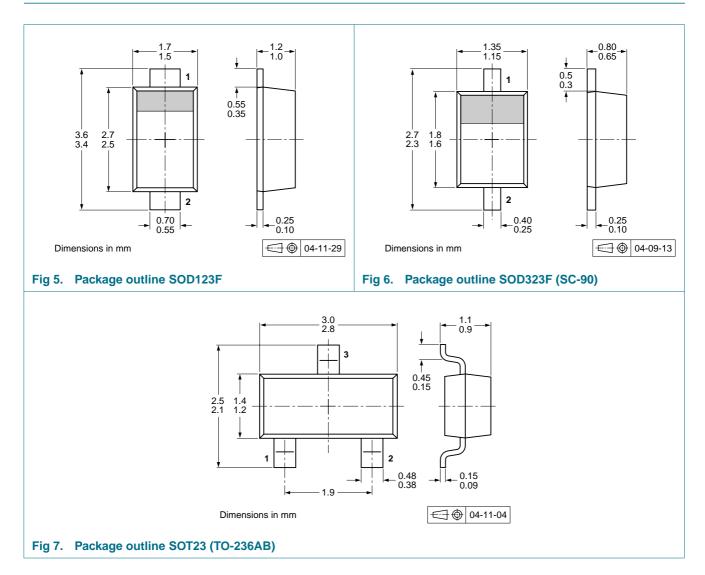
Fig 3. Diode capacitance as a function of reverse voltage; typical values

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8. Test information



9. Package outline



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10. Packing information

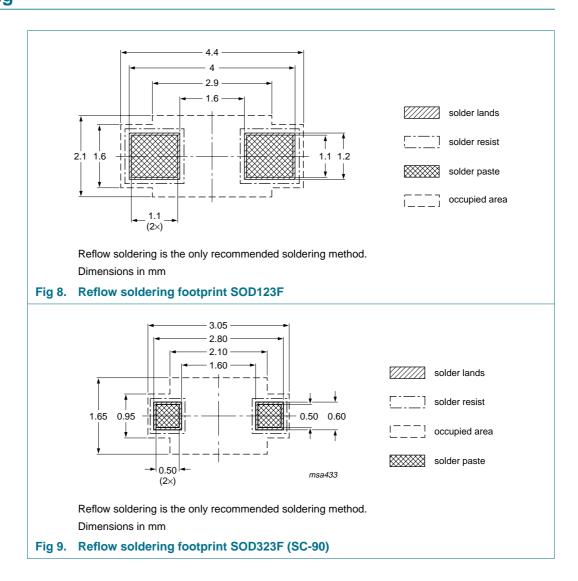
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	quantity
			3000	10000
PMEG4010EH	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135
PMEG4010EJ	SOD323F	4 mm pitch, 8 mm tape and reel	-115	-135
PMEG4010ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

^[1] For further information and the availability of packing methods, see Section 14.

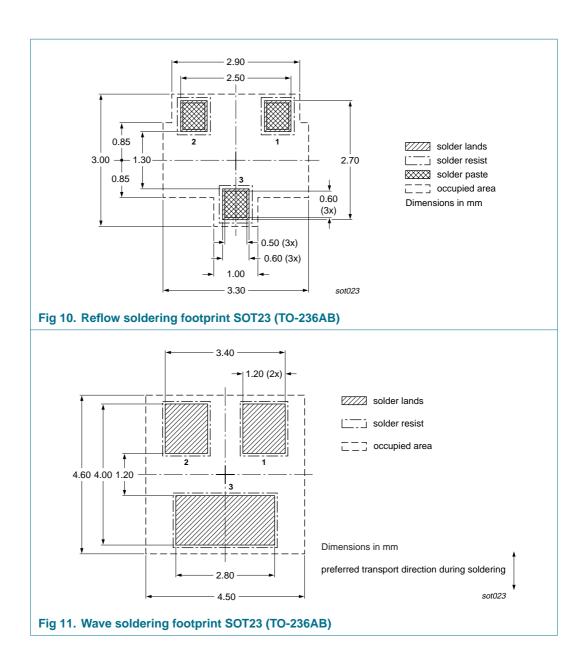
11. Soldering



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PMEG4010EH/EJ/ET

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12. Revision history

Table 10. Revision history

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG4010EH_EJ_ET_4	20070321	Product data sheet	-	PMEGXX10EH_EJ_SER_3
Modifications:		of this data sheet has be of NXP Semiconductors.	een redesigned to com	ply with the new identity
	 Legal texts 	have been adapted to th	e new company name	where appropriate.
	* *	ers PMEG4010EH and P 0EH_EJ_SER_3	MEG4010EJ separate	ed from data sheet
	 Type numb 	er PMEG4010ET added		
	Section 1.1 "General description": amended			
	 Section 1.2 	"Features": amended		
	 Section 1.3 	"Applications": amended	t	
	Section 8 "	Test information": added		
	• Figure 7, 1	<u>0</u> and <u>11</u> : added		
	Section 13	"Legal information": upda	ated	
PMEGXX10EH_EJ_SER_3	20050411	Product data sheet	-	PMEGXX10EJ_SER_2
PMEGXX10EJ_SER_2	20050131	Product data sheet	-	PMEGXX10EJ_SER_1
PMEGXX10EJ_SER_1	20040907	Objective data sheet	-	-

PMEG4010EH/EJ/ET

1 A very low V_F MEGA Schottky barrier rectifiers

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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